



ALPHA & OMEGA
SEMICONDUCTOR



AOU403

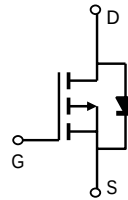
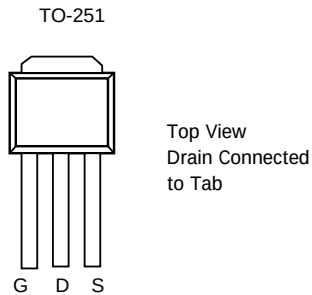
P-Channel Enhancement Mode Field Effect Transistor

General Description

The AOU403 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications. *Standard Product AOU403 is Pb-free (meets ROHS & Sony 259 specifications). AOU403L is a Green Product ordering option. AOU403 and AOU403L are electrically identical.*

Features

V_{DS} (V) = -60V
 I_D = -12A (V_{GS} = -10V)
 $R_{DS(ON)} < 115m\Omega$ (V_{GS} = -10V)
 $R_{DS(ON)} < 150m\Omega$ (V_{GS} = -4.5V)



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^G	I_D	$T_C=25^\circ\text{C}$ -12	A
		$T_C=100^\circ\text{C}$ -10	
Pulsed Drain Current ^C	I_{DM}	-30	
Avalanche Current ^C	I_{AR}	-12	A
Repetitive avalanche energy $L=0.1mH$ ^C	E_{AR}	23	mJ
Power Dissipation ^B	P_D	$T_C=25^\circ\text{C}$ 50	W
		$T_C=100^\circ\text{C}$ 25	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	$^\circ\text{C}$

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	Steady-State	$R_{\theta JA}$	105	125	$^\circ\text{C/W}$
Maximum Junction-to-Case ^B	Steady-State	$R_{\theta JC}$	2.5	3	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =-250μA, V _{GS} =0V	-60			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-48V, V _{GS} =0V T _J =55°C		-0.003	-1 -5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±20V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1.5	-2.1	-3	V
I _{D(ON)}	On state drain current	V _{GS} =-10V, V _{DS} =-5V	-30			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-10V, I _D =-12A T _J =125°C		91 150	115	mΩ
		V _{GS} =-4.5V, I _D =-8A		114	150	mΩ
g _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-12A		12.8		S
V _{SD}	Diode Forward Voltage	I _S =-1A, V _{GS} =0V		-0.76	-1	V
I _S	Maximum Body-Diode Continuous Current				-12	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-30V, f=1MHz		987	1185	pF
C _{oss}	Output Capacitance			114		pF
C _{rss}	Reverse Transfer Capacitance			46		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		7	10	Ω
SWITCHING PARAMETERS						
Q _g (10V)	Total Gate Charge (10V)	V _{GS} =-10V, V _{DS} =-30V, I _D =-12A		15.8	20	nC
Q _g (4.5V)	Total Gate Charge (4.5V)			7.4	9	nC
Q _{gs}	Gate Source Charge			3		nC
Q _{gd}	Gate Drain Charge			3.5		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =-10V, V _{DS} =-30V, R _L =2.5Ω, R _{GEN} =3Ω		9		ns
t _r	Turn-On Rise Time			10		ns
t _{D(off)}	Turn-Off DelayTime			25		ns
t _f	Turn-Off Fall Time			11		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =-12A, dI/dt=100A/μs		27.5	35	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =-12A, dI/dt=100A/μs		30		nC

A: The value of R qJA is measured with the device in a still air environment with T_A=25°C.

B: The power dissipation PD is based on T_J(MAX)=175°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C: Repetitive rating, pulse width limited by junction temperature T_J(MAX)=175°C.

D: The R qJA is the sum of the thermal impedance from junction to case R qJC and case to ambient.

E: The static characteristics in Figures 1 to 6 are obtained using <300 ms pulses, duty cycle 0.5% max.

F: These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_J(MAX)=175°C.

G: The maximum current rating is limited by bond-wires.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

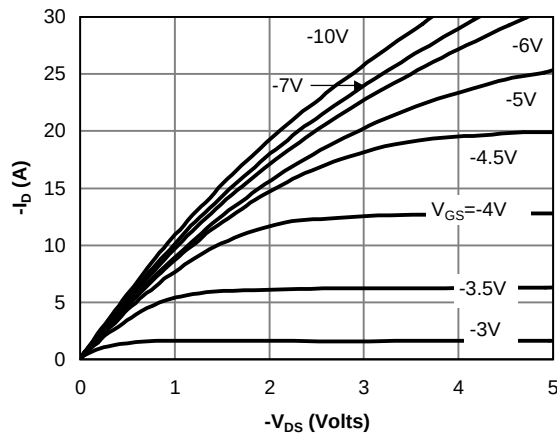


Fig 1: On-Region Characteristics

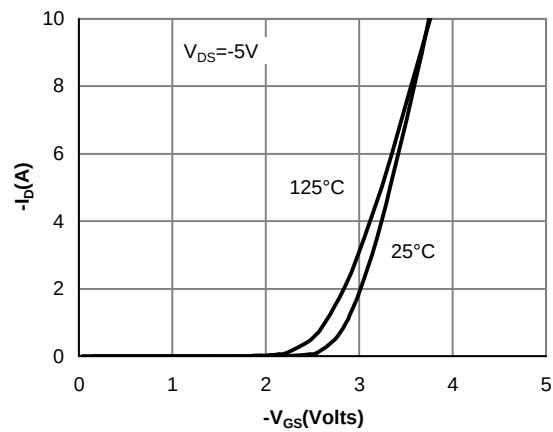


Figure 2: Transfer Characteristics

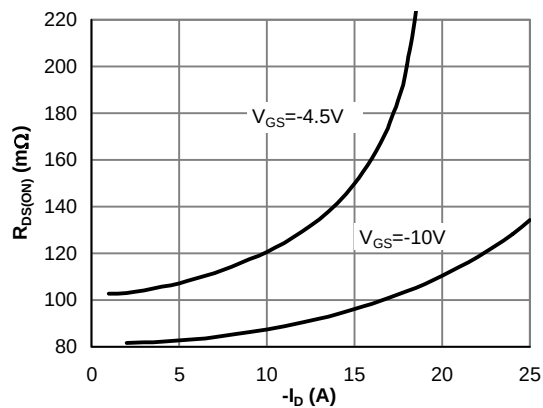


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

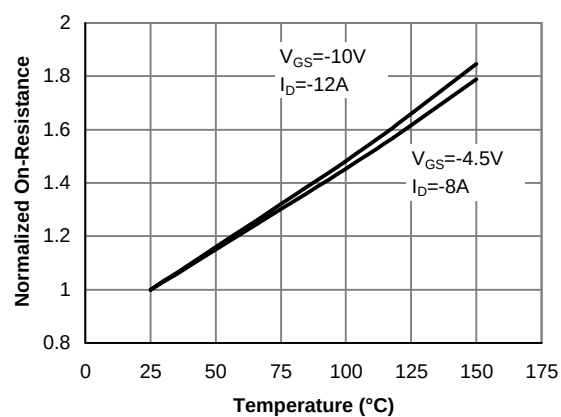


Figure 4: On-Resistance vs. Junction Temperature

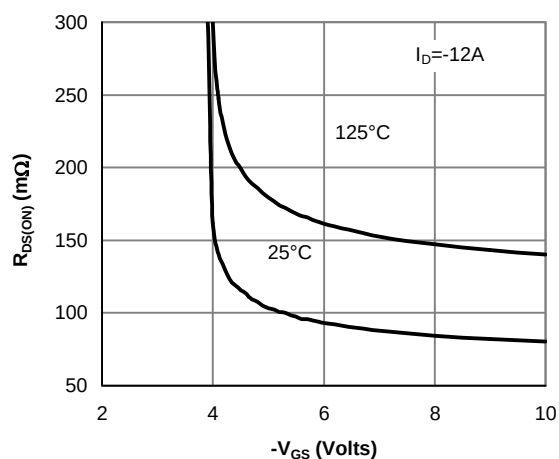


Figure 5: On-Resistance vs. Gate-Source Voltage

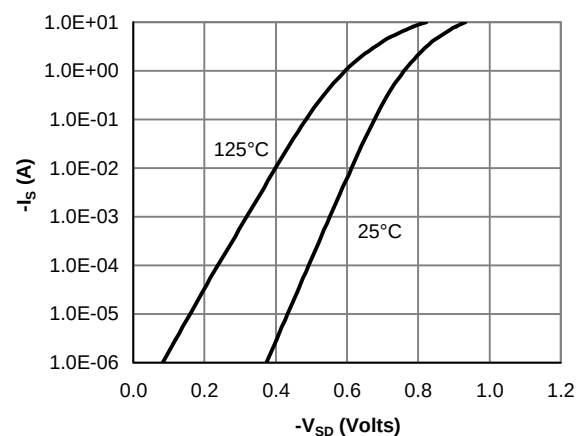


Figure 6: Body-Diode Characteristics

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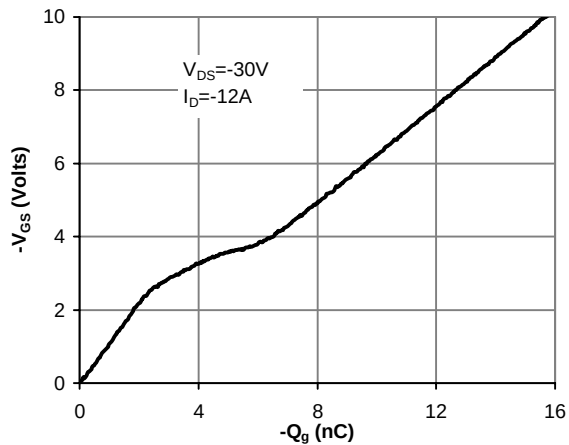


Figure 7: Gate-Charge Characteristics

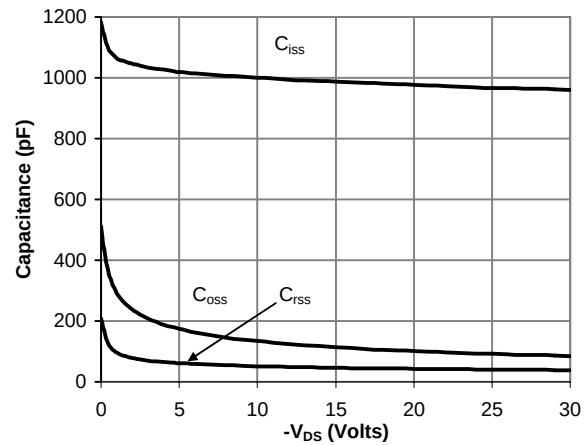


Figure 8: Capacitance Characteristics

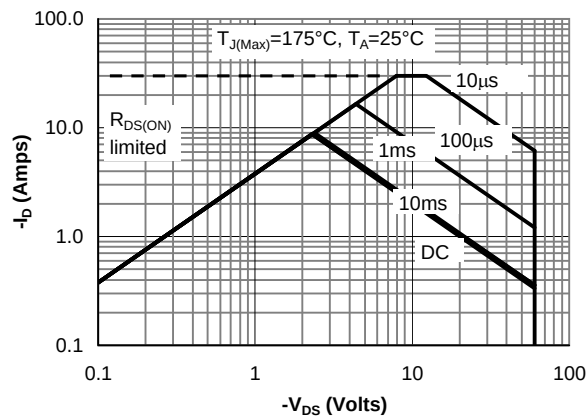


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

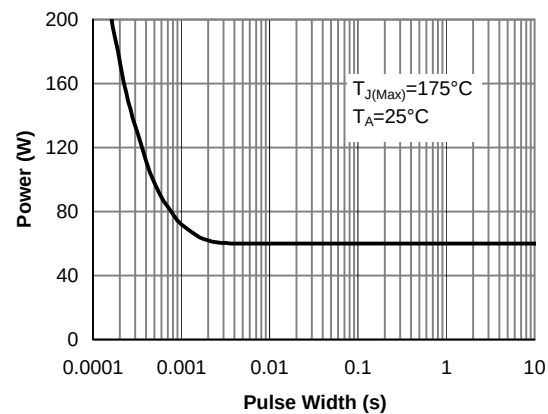


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

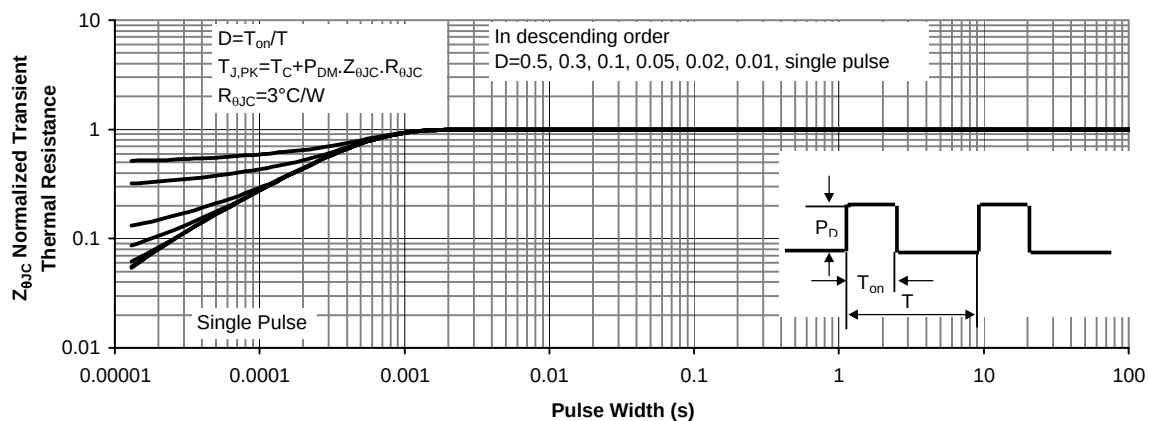


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

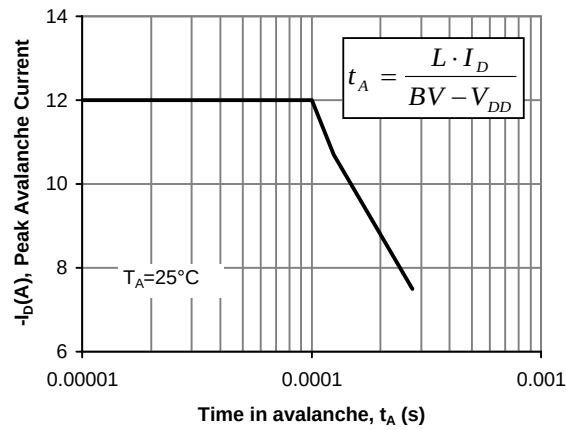


Figure 12: Single Pulse Avalanche capability

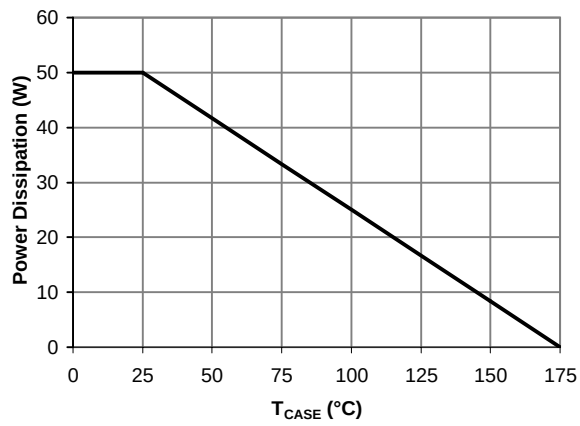


Figure 13: Power De-rating (Note B)

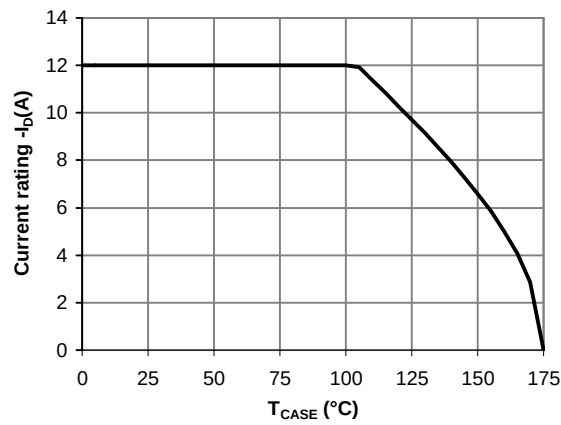


Figure 14: Current De-rating (Note B)